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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

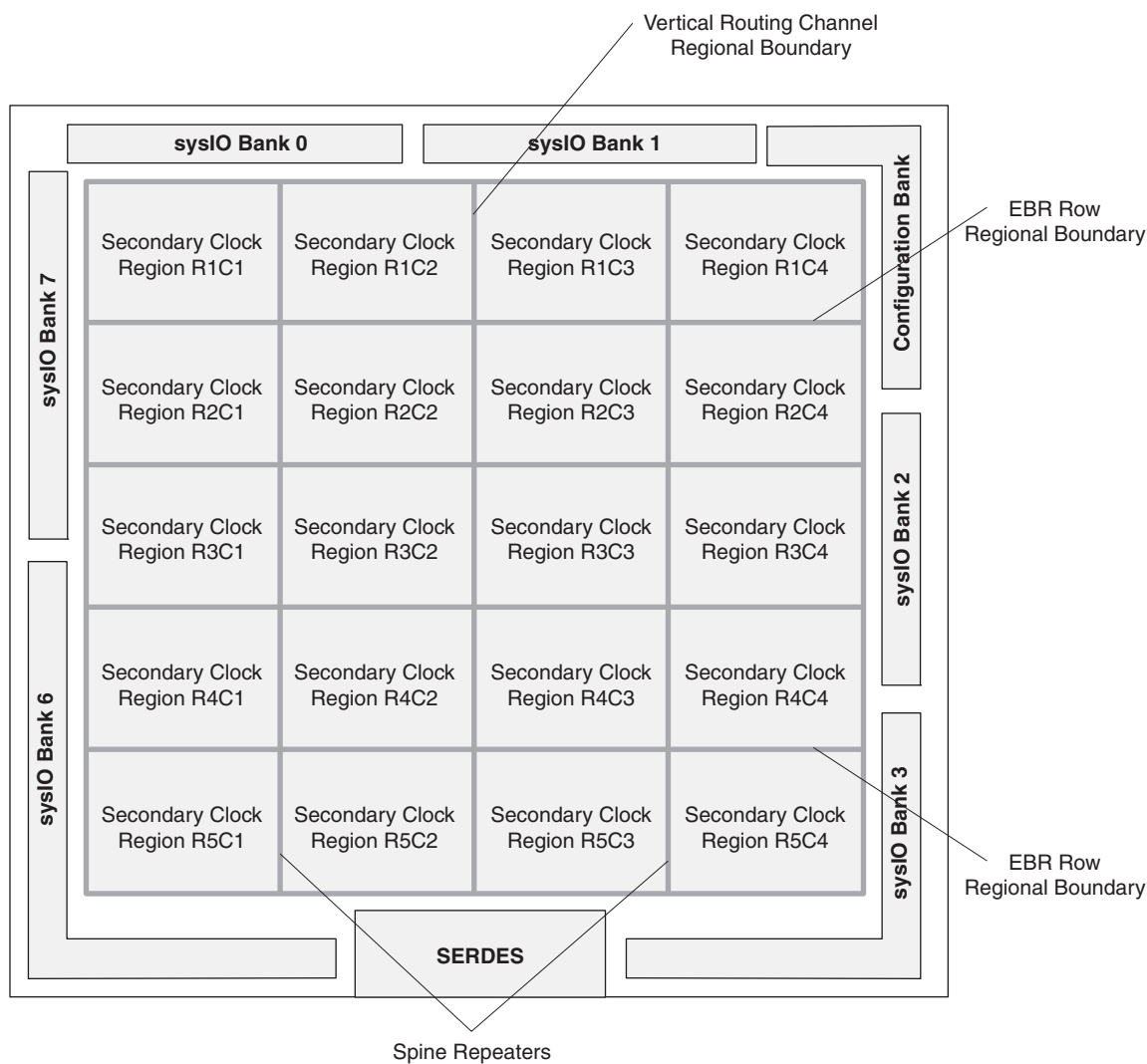
Details

Product Status	Obsolete
Number of LABs/CLBs	18625
Number of Logic Elements/Cells	149000
Total RAM Bits	7014400
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-150ea-7fn672itw

Table 2-6. Secondary Clock Regions

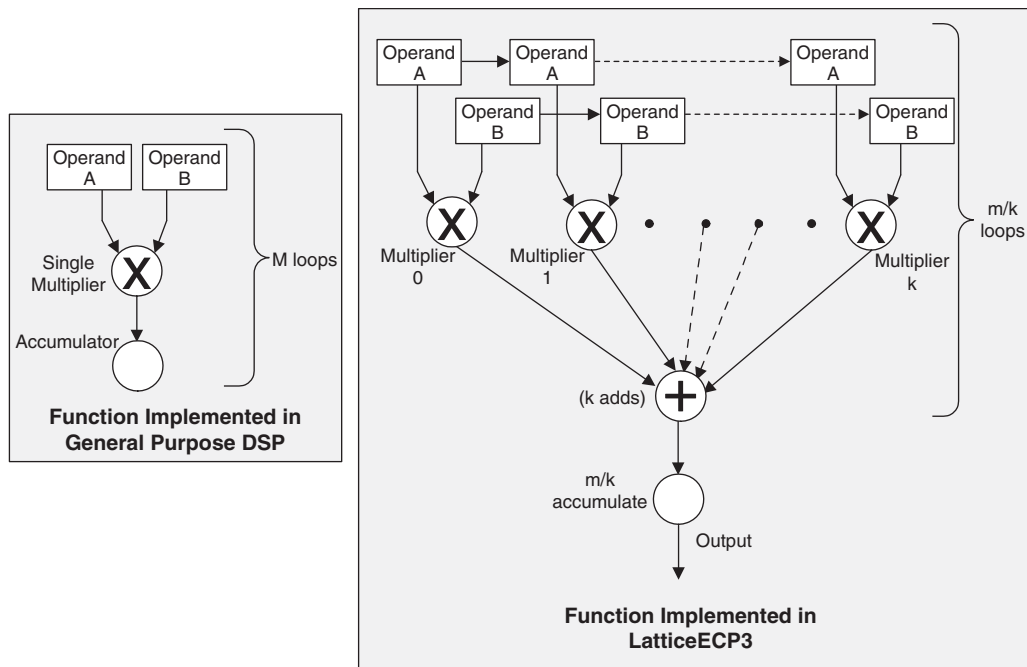
Device	Number of Secondary Clock Regions
ECP3-17	16
ECP3-35	16
ECP3-70	20
ECP3-95	20
ECP3-150	36

Figure 2-15. LatticeECP3-70 and LatticeECP3-95 Secondary Clock Regions



This allows designers to use highly parallel implementations of DSP functions. Designers can optimize DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2-23 compares the fully serial implementation to the mixed parallel and serial implementation.

Figure 2-23. Comparison of General DSP and LatticeECP3 Approaches



LatticeECP3 sysDSP Slice Architecture Features

The LatticeECP3 sysDSP Slice has been significantly enhanced to provide functions needed for advanced processing applications. These enhancements provide improved flexibility and resource utilization.

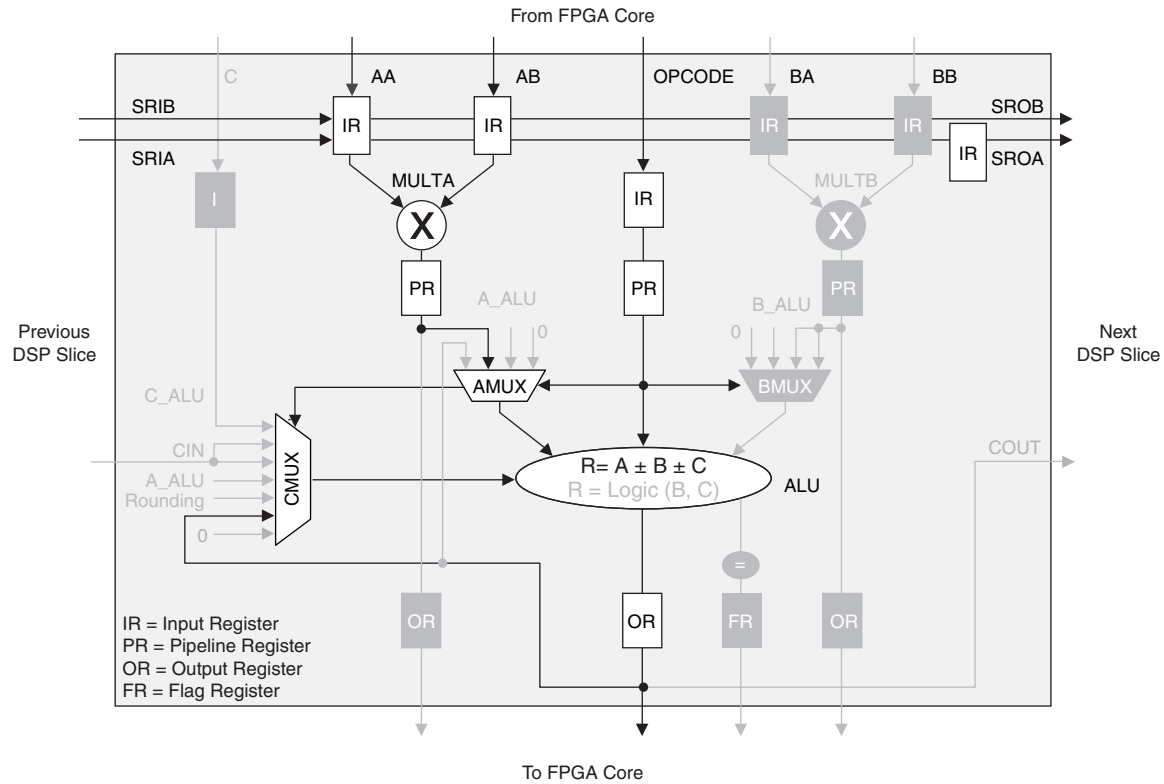
The LatticeECP3 sysDSP Slice supports many functions that include the following:

- Multiply (one 18 x 36, two 18 x 18 or four 9 x 9 Multiplies per Slice)
- Multiply (36 x 36 by cascading across two sysDSP slices)
- Multiply Accumulate (up to 18 x 36 Multipliers feeding an Accumulator that can have up to 54-bit resolution)
- Two Multiplies feeding one Accumulate per cycle for increased processing with lower latency (two 18 x 18 Multiplies feed into an accumulator that can accumulate up to 52 bits)
- Flexible saturation and rounding options to satisfy a diverse set of applications situations
- Flexible cascading across DSP slices
 - Minimizes fabric use for common DSP and ALU functions
 - Enables implementation of FIR Filter or similar structures using dedicated sysDSP slice resources only
 - Provides matching pipeline registers
 - Can be configured to continue cascading from one row of sysDSP slices to another for longer cascade chains
- Flexible and Powerful Arithmetic Logic Unit (ALU) Supports:
 - Dynamically selectable ALU OPCODE
 - Ternary arithmetic (addition/subtraction of three inputs)
 - Bit-wise two-input logic operations (AND, OR, NAND, NOR, XOR and XNOR)
 - Eight flexible and programmable ALU flags that can be used for multiple pattern detection scenarios, such

MAC DSP Element

In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice in the LatticeECP3 family can be initialized dynamically. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-27 shows the MAC sysDSP element.

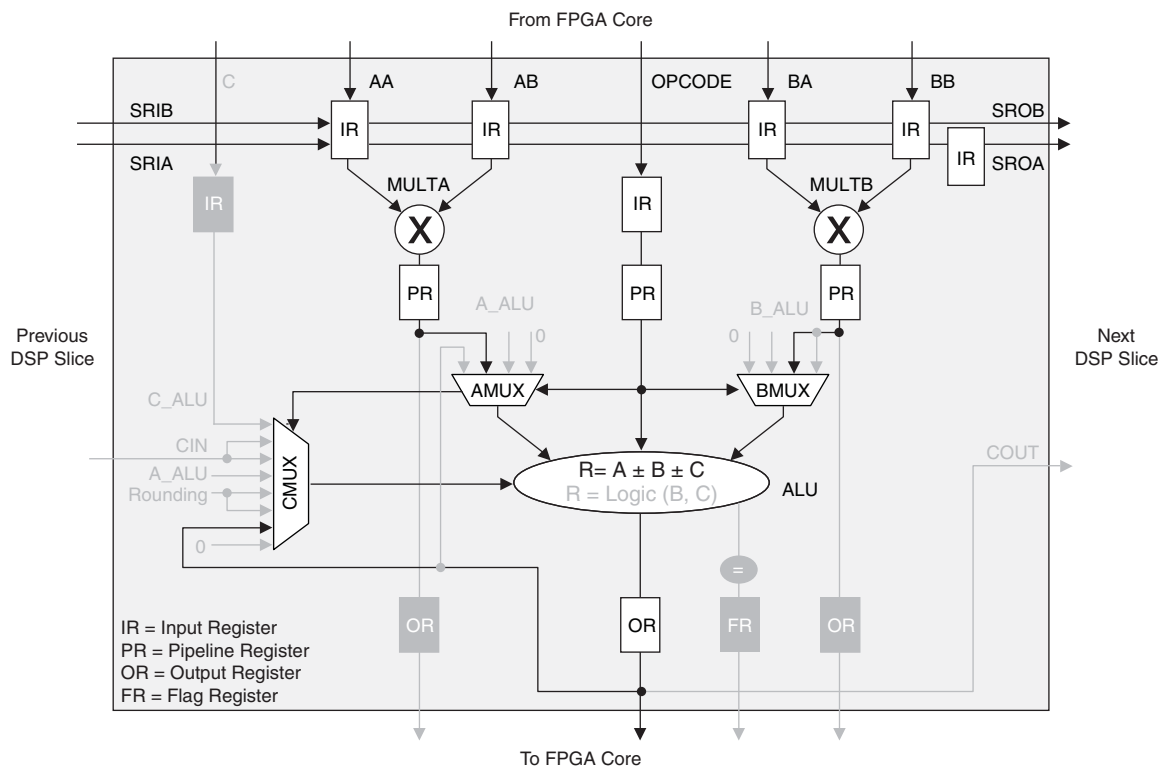
Figure 2-27. MAC DSP Element



MMAC DSP Element

The LatticeECP3 supports a MAC with two multipliers. This is called Multiply Multiply Accumulate or MMAC. In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value and with the result of the multiplier operation of operands BA and BB. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-28 shows the MMAC sysDSP element.

Figure 2-28. MMAC sysDSP Element



ALU Flags

The sysDSP slice provides a number of flags from the ALU including:

- Equal to zero (EQZ)
- Equal to zero with mask (EQZM)
- Equal to one with mask (EQOM)
- Equal to pattern with mask (EQPAT)
- Equal to bit inverted pattern with mask (EQPATB)
- Accumulator Overflow (OVER)
- Accumulator Underflow (UNDER)
- Either over or under flow supporting LatticeECP2 legacy designs (OVERUNDER)

Clock, Clock Enable and Reset Resources

Global Clock, Clock Enable and Reset signals from routing are available to every sysDSP slice. From four clock sources (CLK0, CLK1, CLK2, and CLK3) one clock is selected for each input register, pipeline register and output register. Similarly Clock Enable (CE) and Reset (RST) are selected at each input register, pipeline register and output register.

Resources Available in the LatticeECP3 Family

Table 2-9 shows the maximum number of multipliers for each member of the LatticeECP3 family. Table 2-10 shows the maximum available EBR RAM Blocks in each LatticeECP3 device. EBR blocks, together with Distributed RAM can be used to store variables locally for fast DSP operations.

Table 2-9. Maximum Number of DSP Slices in the LatticeECP3 Family

Device	DSP Slices	9x9 Multiplier	18x18 Multiplier	36x36 Multiplier
ECP3-17	12	48	24	6
ECP3-35	32	128	64	16
ECP3-70	64	256	128	32
ECP3-95	64	256	128	32
ECP3-150	160	640	320	80

Table 2-10. Embedded SRAM in the LatticeECP3 Family

Device	EBR SRAM Block	Total EBR SRAM (Kbits)
ECP3-17	38	700
ECP3-35	72	1327
ECP3-70	240	4420
ECP3-95	240	4420
ECP3-150	372	6850

Figure 2-40. SERDES/PCS Quads (LatticeECP3-150)

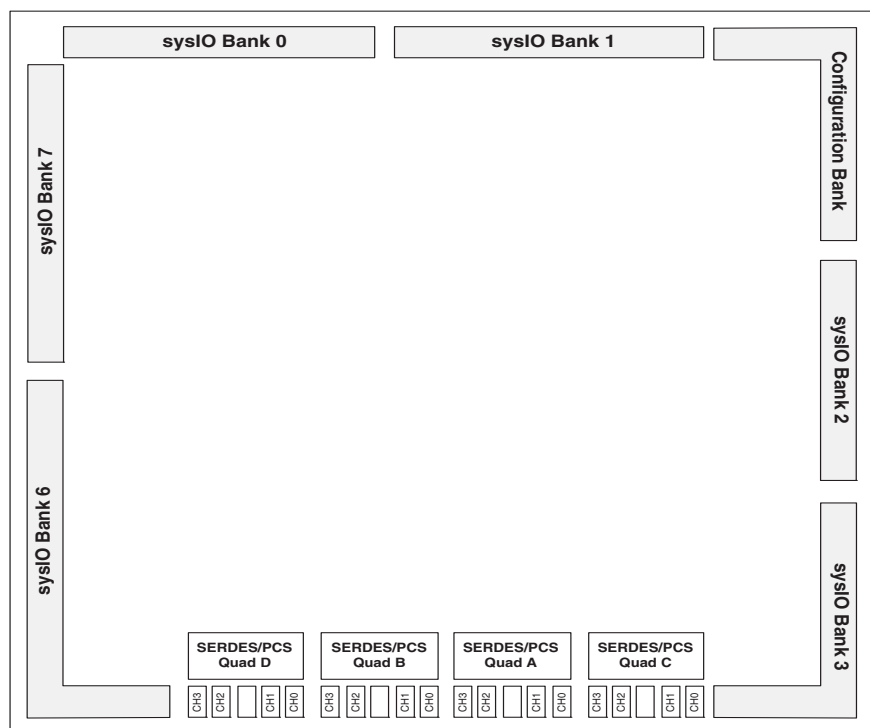


Table 2-13. LatticeECP3 SERDES Standard Support

Standard	Data Rate (Mbps)	Number of General/Link Width	Encoding Style
PCI Express 1.1	2500	x1, x2, x4	8b10b
Gigabit Ethernet	1250, 2500	x1	8b10b
SGMII	1250	x1	8b10b
XAUI	3125	x4	8b10b
Serial RapidIO Type I, Serial RapidIO Type II, Serial RapidIO Type III	1250, 2500, 3125	x1, x4	8b10b
CPRI-1, CPRI-2, CPRI-3, CPRI-4	614.4, 1228.8, 2457.6, 3072.0	x1	8b10b
SD-SDI (259M, 344M)	143 ¹ , 177 ¹ , 270, 360, 540	x1	NRZI/Scrambled
HD-SDI (292M)	1483.5, 1485	x1	NRZI/Scrambled
3G-SDI (424M)	2967, 2970	x1	NRZI/Scrambled
SONET-ST5-3 ²	155.52	x1	N/A
SONET-ST5-12 ²	622.08	x1	N/A
SONET-ST5-48 ²	2488	x1	N/A

1. For slower rates, the SERDES are bypassed and CML signals are directly connected to the FPGA routing.

2. The SONET protocol is supported in 8-bit SERDES mode. See TN1176 [Lattice ECP3 SERDES/PCS Usage Guide](#) for more information.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$I_{IL}, I_{IH}^{1,4}$	Input or I/O Low Leakage	$0 \leq V_{IN} \leq (V_{CCIO} - 0.2 \text{ V})$	—	—	10	μA
$I_{IH}^{1,3}$	Input or I/O High Leakage	$(V_{CCIO} - 0.2 \text{ V}) < V_{IN} \leq 3.6 \text{ V}$	—	—	150	μA
I_{PU}	I/O Active Pull-up Current	$0 \leq V_{IN} \leq 0.7 V_{CCIO}$	-30	—	-210	μA
I_{PD}	I/O Active Pull-down Current	$V_{IL} (\text{MAX}) \leq V_{IN} \leq V_{CCIO}$	30	—	210	μA
I_{BHLS}	Bus Hold Low Sustaining Current	$V_{IN} = V_{IL} (\text{MAX})$	30	—	—	μA
I_{BHHS}	Bus Hold High Sustaining Current	$V_{IN} = 0.7 V_{CCIO}$	-30	—	—	μA
I_{BHLO}	Bus Hold Low Overdrive Current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	210	μA
I_{BHHO}	Bus Hold High Overdrive Current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	-210	μA
V_{BHT}	Bus Hold Trip Points	$0 \leq V_{IN} \leq V_{IH} (\text{MAX})$	$V_{IL} (\text{MAX})$	—	$V_{IH} (\text{MIN})$	V
C1	I/O Capacitance ²	$V_{CCIO} = 3.3 \text{ V}, 2.5 \text{ V}, 1.8 \text{ V}, 1.5 \text{ V}, 1.2 \text{ V},$ $V_{CC} = 1.2 \text{ V}, V_{IO} = 0 \text{ to } V_{IH} (\text{MAX})$	—	5	8	pf
C2	Dedicated Input Capacitance ²	$V_{CCIO} = 3.3 \text{ V}, 2.5 \text{ V}, 1.8 \text{ V}, 1.5 \text{ V}, 1.2 \text{ V},$ $V_{CC} = 1.2 \text{ V}, V_{IO} = 0 \text{ to } V_{IH} (\text{MAX})$	—	5	7	pf

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.

2. $T_A = 25^\circ\text{C}$, $f = 1.0 \text{ MHz}$.

3. Applicable to general purpose I/Os in top and bottom banks.

4. When used as V_{REF} maximum leakage = $25 \mu\text{A}$.

SERDES Power Supply Requirements^{1, 2, 3}

Over Recommended Operating Conditions

Symbol	Description	Typ.	Max.	Units
Standby (Power Down)				
I_{CCA-SB}	V_{CCA} current (per channel)	3	5	mA
$I_{CCIB-SB}$	Input buffer current (per channel)	—	—	mA
$I_{CCOB-SB}$	Output buffer current (per channel)	—	—	mA
Operating (Data Rate = 3.2 Gbps)				
I_{CCA-OP}	V_{CCA} current (per channel)	68	77	mA
$I_{CCIB-OP}$	Input buffer current (per channel)	5	7	mA
$I_{CCOB-OP}$	Output buffer current (per channel)	19	25	mA
Operating (Data Rate = 2.5 Gbps)				
I_{CCA-OP}	V_{CCA} current (per channel)	66	76	mA
$I_{CCIB-OP}$	Input buffer current (per channel)	4	5	mA
$I_{CCOB-OP}$	Output buffer current (per channel)	15	18	mA
Operating (Data Rate = 1.25 Gbps)				
I_{CCA-OP}	V_{CCA} current (per channel)	62	72	mA
$I_{CCIB-OP}$	Input buffer current (per channel)	4	5	mA
$I_{CCOB-OP}$	Output buffer current (per channel)	15	18	mA
Operating (Data Rate = 250 Mbps)				
I_{CCA-OP}	V_{CCA} current (per channel)	55	65	mA
$I_{CCIB-OP}$	Input buffer current (per channel)	4	5	mA
$I_{CCOB-OP}$	Output buffer current (per channel)	14	17	mA
Operating (Data Rate = 150 Mbps)				
I_{CCA-OP}	V_{CCA} current (per channel)	55	65	mA
$I_{CCIB-OP}$	Input buffer current (per channel)	4	5	mA
$I_{CCOB-OP}$	Output buffer current (per channel)	14	17	mA

1. Equalization enabled, pre-emphasis disabled.

2. One quarter of the total quad power (includes contribution from common circuits, all channels in the quad operating, pre-emphasis disabled, equalization enabled).

3. Pre-emphasis adds 20 mA to I_{CCA-OP} data.

MLVDS25

The LatticeECP3 devices support the differential MLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The MLVDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-5 is one possible solution for MLVDS standard implementation. Resistor values in Figure 3-5 are industry standard values for 1% resistors.

Figure 3-5. MLVDS25 (Multipoint Low Voltage Differential Signaling)

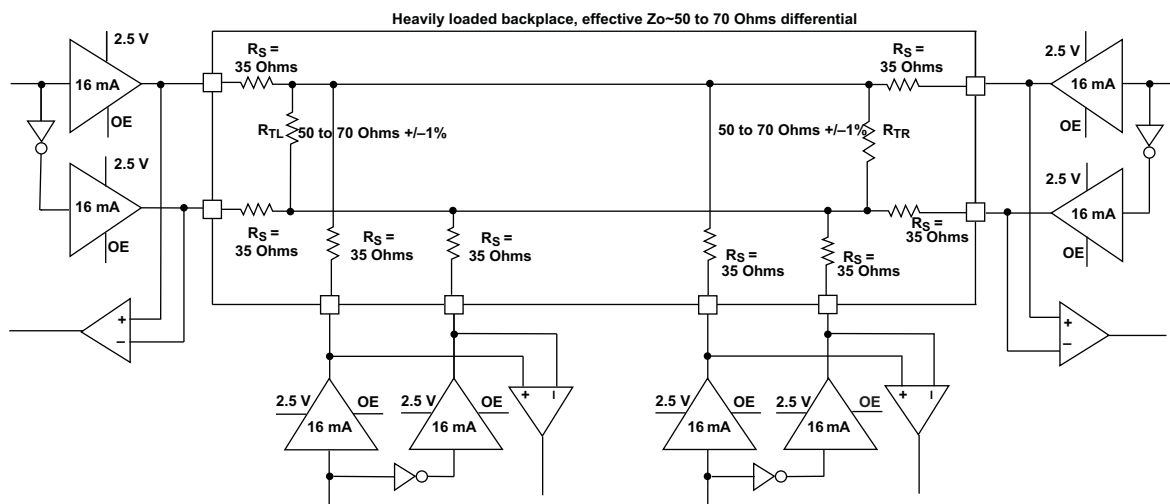


Table 3-5. MLVDS25 DC Conditions¹

Parameter	Description	Typical		Units
		Zo=50Ω	Zo=70Ω	
V _{CCIO}	Output Driver Supply (+/-5%)	2.50	2.50	V
Z _{OUT}	Driver Impedance	10.00	10.00	Ω
R _S	Driver Series Resistor (+/-1%)	35.00	35.00	Ω
R _{TL}	Driver Parallel Resistor (+/-1%)	50.00	70.00	Ω
R _{TR}	Receiver Termination (+/-1%)	50.00	70.00	Ω
V _{OH}	Output High Voltage	1.52	1.60	V
V _{OL}	Output Low Voltage	0.98	0.90	V
V _{OD}	Output Differential Voltage	0.54	0.70	V
V _{CM}	Output Common Mode Voltage	1.25	1.25	V
I _{DC}	DC Output Current	21.74	20.00	mA

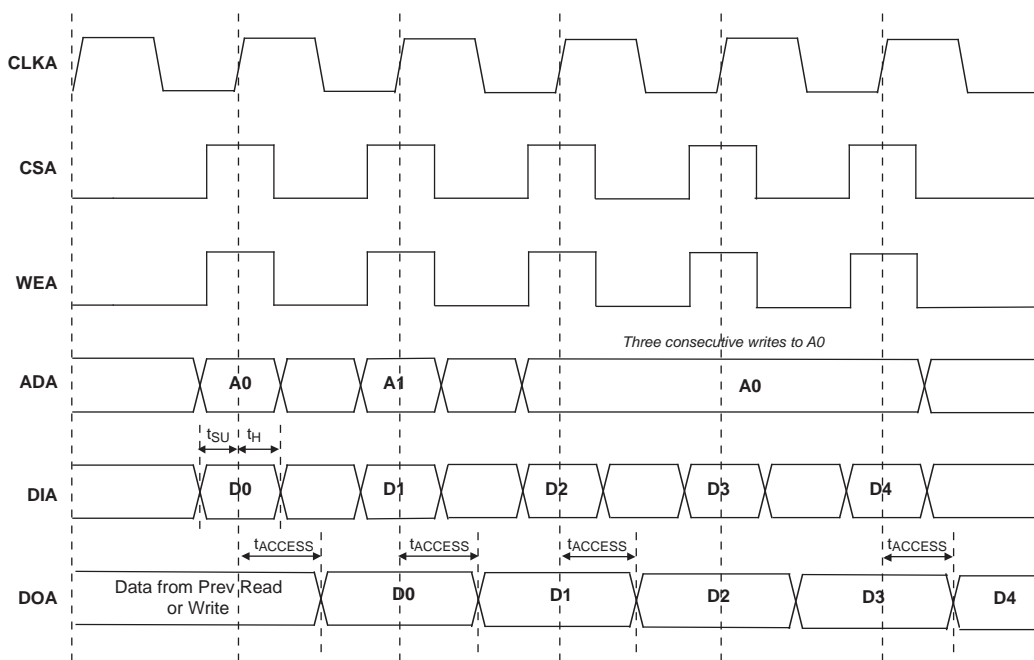
1. For input buffer, see LVDS table.

LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-35EA	683	—	688	—	690	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-35EA	683	—	688	—	690	—	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-17EA	683	—	688	—	690	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-17EA	683	—	688	—	690	—	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDR1 Output with Clock and Data Aligned at Pin (GDDR1_TX.SCLK.Aligned)¹⁰									
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-150EA	—	335	—	338	—	341	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-150EA	—	335	—	338	—	341	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-70EA/95EA	—	339	—	343	—	347	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-70EA/95EA	—	339	—	343	—	347	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-35EA	—	322	—	320	—	321	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-35EA	—	322	—	320	—	321	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-17EA	—	322	—	320	—	321	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-17EA	—	322	—	320	—	321	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDR1 Output with Clock and Data (<10 Bits Wide) Centered at Pin (GDDR1_TX.DQS.Centered)¹⁰									
Left and Right Sides									
t _{DVBGDDR}	Data Valid Before CLK	ECP3-150EA	670	—	670	—	670	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-35EA	670	—	675	—	676	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-35EA	670	—	675	—	676	—	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-17EA	670	—	670	—	670	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-17EA	670	—	670	—	670	—	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDR2 Output with Clock and Data (>10 Bits Wide) Aligned at Pin (GDDR2_TX.Aligned)									
Left and Right Sides									
t _{DIBGDDR}	Data Invalid Before Clock	All ECP3EA Devices	—	200	—	210	—	220	ps
t _{DIAGDDR}	Data Invalid After Clock	All ECP3EA Devices	—	200	—	210	—	220	ps
f _{MAX_GDDR}	DDR2 Clock Frequency	All ECP3EA Devices	—	500	—	420	—	375	MHz
Generic DDR2 Output with Clock and Data (>10 Bits Wide) Centered at Pin Using DQSDLL (GDDR2_TX.DQSDLL.Centered)¹¹									
Left and Right Sides									
t _{DVBGDDR}	Data Valid Before CLK	All ECP3EA Devices	400	—	400	—	431	—	ps
t _{DVAGDDR}	Data Valid After CLK	All ECP3EA Devices	400	—	400	—	432	—	ps
f _{MAX_GDDR}	DDR2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz

Figure 3-11. Write Through (SP Read/Write on Port A, Input Registers Only)



Note: Input data and address are registered at the positive edge of the clock and output data appears after the positive edge of the clock.

LatticeECP3 Family Timing Adders^{1, 2, 3, 4, 5, 7} (Continued)
Over Recommended Commercial Operating Conditions

Buffer Type	Description	–8	–7	–6	Units
LVC MOS15_4mA	LVC MOS 1.5 4 mA drive, fast slew rate	0.21	0.25	0.29	ns
LVC MOS15_8mA	LVC MOS 1.5 8 mA drive, fast slew rate	0.05	0.07	0.09	ns
LVC MOS12_2mA	LVC MOS 1.2 2 mA drive, fast slew rate	0.43	0.51	0.59	ns
LVC MOS12_6mA	LVC MOS 1.2 6 mA drive, fast slew rate	0.23	0.28	0.33	ns
LVC MOS33_4mA	LVC MOS 3.3 4 mA drive, slow slew rate	1.44	1.58	1.72	ns
LVC MOS33_8mA	LVC MOS 3.3 8 mA drive, slow slew rate	0.98	1.10	1.22	ns
LVC MOS33_12mA	LVC MOS 3.3 12 mA drive, slow slew rate	0.67	0.77	0.86	ns
LVC MOS33_16mA	LVC MOS 3.3 16 mA drive, slow slew rate	0.97	1.09	1.21	ns
LVC MOS33_20mA	LVC MOS 3.3 20 mA drive, slow slew rate	0.67	0.76	0.85	ns
LVC MOS25_4mA	LVC MOS 2.5 4 mA drive, slow slew rate	1.48	1.63	1.78	ns
LVC MOS25_8mA	LVC MOS 2.5 8 mA drive, slow slew rate	1.02	1.14	1.27	ns
LVC MOS25_12mA	LVC MOS 2.5 12 mA drive, slow slew rate	0.74	0.84	0.94	ns
LVC MOS25_16mA	LVC MOS 2.5 16 mA drive, slow slew rate	1.02	1.14	1.26	ns
LVC MOS25_20mA	LVC MOS 2.5 20 mA drive, slow slew rate	0.74	0.83	0.93	ns
LVC MOS18_4mA	LVC MOS 1.8 4 mA drive, slow slew rate	1.60	1.77	1.93	ns
LVC MOS18_8mA	LVC MOS 1.8 8 mA drive, slow slew rate	1.11	1.25	1.38	ns
LVC MOS18_12mA	LVC MOS 1.8 12 mA drive, slow slew rate	0.87	0.98	1.09	ns
LVC MOS18_16mA	LVC MOS 1.8 16 mA drive, slow slew rate	0.86	0.97	1.07	ns
LVC MOS15_4mA	LVC MOS 1.5 4 mA drive, slow slew rate	1.71	1.89	2.08	ns
LVC MOS15_8mA	LVC MOS 1.5 8 mA drive, slow slew rate	1.20	1.34	1.48	ns
LVC MOS12_2mA	LVC MOS 1.2 2 mA drive, slow slew rate	1.37	1.56	1.74	ns
LVC MOS12_6mA	LVC MOS 1.2 6 mA drive, slow slew rate	1.11	1.27	1.43	ns
PCI33	PCI, VCCIO = 3.3 V	–0.12	–0.13	–0.14	ns

1. Timing adders are characterized but not tested on every device.
2. LVC MOS timing measured with the load specified in Switching Test Condition table.
3. All other standards tested according to the appropriate specifications.
4. Not all I/O standards and drive strengths are supported for all banks. See the Architecture section of this data sheet for details.
5. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
6. This data does not apply to the LatticeECP3-17EA device.
7. For details on –9 speed grade devices, please contact your Lattice Sales Representative.

LatticeECP3 Maximum I/O Buffer Speed ^{1, 2, 3, 4, 5, 6}

Over Recommended Operating Conditions

Buffer	Description	Max.	Units
Maximum Input Frequency			
LVDS25	LVDS, $V_{CCIO} = 2.5\text{ V}$	400	MHz
MLVDS25	MLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	400	MHz
BLVDS25	BLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	400	MHz
PPLVDS	Point-to-Point LVDS	400	MHz
TRLVDS	Transition-Reduced LVDS	612	MHz
Mini LVDS	Mini LVDS	400	MHz
LVPECL33	LVPECL, Emulated, $V_{CCIO} = 3.3\text{ V}$	400	MHz
HSTL18 (all supported classes)	HSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	400	MHz
HSTL15	HSTL_15 class I, $V_{CCIO} = 1.5\text{ V}$	400	MHz
SSTL33 (all supported classes)	SSTL_3 class I, II, $V_{CCIO} = 3.3\text{ V}$	400	MHz
SSTL25 (all supported classes)	SSTL_2 class I, II, $V_{CCIO} = 2.5\text{ V}$	400	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	400	MHz
LVTTL33	LVTTL, $V_{CCIO} = 3.3\text{ V}$	166	MHz
LVC MOS33	LVC MOS, $V_{CCIO} = 3.3\text{ V}$	166	MHz
LVC MOS25	LVC MOS, $V_{CCIO} = 2.5\text{ V}$	166	MHz
LVC MOS18	LVC MOS, $V_{CCIO} = 1.8\text{ V}$	166	MHz
LVC MOS15	LVC MOS 1.5, $V_{CCIO} = 1.5\text{ V}$	166	MHz
LVC MOS12	LVC MOS 1.2, $V_{CCIO} = 1.2\text{ V}$	166	MHz
PCI33	PCI, $V_{CCIO} = 3.3\text{ V}$	66	MHz
Maximum Output Frequency			
LVDS25E	LVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	300	MHz
LVDS25	LVDS, $V_{CCIO} = 2.5\text{ V}$	612	MHz
MLVDS25	MLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	300	MHz
RS DS25	RS DS, Emulated, $V_{CCIO} = 2.5\text{ V}$	612	MHz
BLVDS25	BLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	300	MHz
PPLVDS	Point-to-point LVDS	612	MHz
LVPECL33	LVPECL, Emulated, $V_{CCIO} = 3.3\text{ V}$	612	MHz
Mini-LVDS	Mini LVDS	612	MHz
HSTL18 (all supported classes)	HSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	200	MHz
HSTL15 (all supported classes)	HSTL_15 class I, $V_{CCIO} = 1.5\text{ V}$	200	MHz
SSTL33 (all supported classes)	SSTL_3 class I, II, $V_{CCIO} = 3.3\text{ V}$	233	MHz
SSTL25 (all supported classes)	SSTL_2 class I, II, $V_{CCIO} = 2.5\text{ V}$	233	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	266	MHz
LVTTL33	LVTTL, $V_{CCIO} = 3.3\text{ V}$	166	MHz
LVC MOS33 (For all drives)	LVC MOS, 3.3 V	166	MHz
LVC MOS25 (For all drives)	LVC MOS, 2.5 V	166	MHz
LVC MOS18 (For all drives)	LVC MOS, 1.8 V	166	MHz
LVC MOS15 (For all drives)	LVC MOS, 1.5 V	166	MHz
LVC MOS12 (For all drives except 2 mA)	LVC MOS, $V_{CCIO} = 1.2\text{ V}$	166	MHz
LVC MOS12 (2 mA drive)	LVC MOS, $V_{CCIO} = 1.2\text{ V}$	100	MHz

DLL Timing

Over Recommended Operating Conditions

Parameter	Description	Condition	Min.	Typ.	Max.	Units
f_{REF}	Input reference clock frequency (on-chip or off-chip)		133	—	500	MHz
f_{FB}	Feedback clock frequency (on-chip or off-chip)		133	—	500	MHz
f_{CLKOP}^1	Output clock frequency, CLKOP		133	—	500	MHz
f_{CLKOS}^2	Output clock frequency, CLKOS		33.3	—	500	MHz
t_{PJIT}	Output clock period jitter (clean input)			—	200	ps p-p
t_{DUTY}	Output clock duty cycle (at 50% levels, 50% duty cycle input clock, 50% duty cycle circuit turned off, time reference delay mode)	Edge Clock	40		60	%
		Primary Clock	30		70	%
$t_{DUTYTRD}$	Output clock duty cycle (at 50% levels, arbitrary duty cycle input clock, 50% duty cycle circuit enabled, time reference delay mode)	Primary Clock < 250 MHz	45		55	%
		Primary Clock ≥ 250 MHz	30		70	%
		Edge Clock	45		55	%
$t_{DUTYCIR}$	Output clock duty cycle (at 50% levels, arbitrary duty cycle input clock, 50% duty cycle circuit enabled, clock injection removal mode) with DLL cascading	Primary Clock < 250 MHz	40		60	%
		Primary Clock ≥ 250 MHz	30		70	%
		Edge Clock	45		55	%
t_{SKEW}^3	Output clock to clock skew between two outputs with the same phase setting		—	—	100	ps
t_{PHASE}	Phase error measured at device pads between off-chip reference clock and feedback clocks		—	—	+/-400	ps
t_{PWH}	Input clock minimum pulse width high (at 80% level)		550	—	—	ps
t_{PWL}	Input clock minimum pulse width low (at 20% level)		550	—	—	ps
t_{INSTB}	Input clock period jitter		—	—	500	ps
t_{LOCK}	DLL lock time		8	—	8200	cycles
t_{RSWD}	Digital reset minimum pulse width (at 80% level)		3	—	—	ns
t_{DEL}	Delay step size		27	45	70	ps
t_{RANGE1}	Max. delay setting for single delay block (64 taps)		1.9	3.1	4.4	ns
t_{RANGE4}	Max. delay setting for four chained delay blocks		7.6	12.4	17.6	ns

1. CLKOP runs at the same frequency as the input clock.

2. CLKOS minimum frequency is obtained with divide by 4.

3. This is intended to be a “path-matching” design guideline and is not a measurable specification.

SERDES High Speed Data Receiver

Table 3-9. Serial Input Data Specifications

Symbol	Description	Min.	Typ.	Max.	Units
RX-CID _S	Stream of nontransitions ¹ (CID = Consecutive Identical Digits) @ 10 ⁻¹² BER	3.125 G	—	136	Bits
		2.5 G	—	144	
		1.485 G	—	160	
		622 M	—	204	
		270 M	—	228	
		150 M	—	296	
V _{RX-DIFF-S}	Differential input sensitivity	150	—	1760	mV, p-p
V _{RX-IN}	Input levels	0	—	V _{CCA} +0.5 ⁴	V
V _{RX-CM-DC}	Input common mode range (DC coupled)	0.6	—	V _{CCA}	V
V _{RX-CM-AC}	Input common mode range (AC coupled) ³	0.1	—	V _{CCA} +0.2	V
T _{RX-RELOCK}	SCDR re-lock time ²	—	1000	—	Bits
Z _{RX-TERM}	Input termination 50/75 Ohm/High Z	-20%	50/75/HiZ	+20%	Ohms
RL _{RX-RL}	Return loss (without package)	10	—	—	dB

1. This is the number of bits allowed without a transition on the incoming data stream when using DC coupling.

2. This is the typical number of bit times to re-lock to a new phase or frequency within +/- 300 ppm, assuming 8b10b encoded data.

3. AC coupling is used to interface to LVPECL and LVDS. LVDS interfaces are found in laser drivers and Fibre Channel equipment. LVDS interfaces are generally found in 622 Mbps SERDES devices.

4. Up to 1.76 V.

Input Data Jitter Tolerance

A receiver's ability to tolerate incoming signal jitter is very dependent on jitter type. High speed serial interface standards have recognized the dependency on jitter type and have specifications to indicate tolerance levels for different jitter types as they relate to specific protocols. Sinusoidal jitter is considered to be a worst case jitter type.

Table 3-10. Receiver Total Jitter Tolerance Specification

Description	Frequency	Condition	Min.	Typ.	Max.	Units
Deterministic	3.125 Gbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p
Deterministic	2.5 Gbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p
Deterministic	1.25 Gbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p
Deterministic	622 Mbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p

Note: Values are measured with CJPAT, all channels operating, FPGA Logic active, I/Os around SERDES pins quiet, voltages are nominal, room temperature.

Figure 3-14. Jitter Transfer – 3.125 Gbps

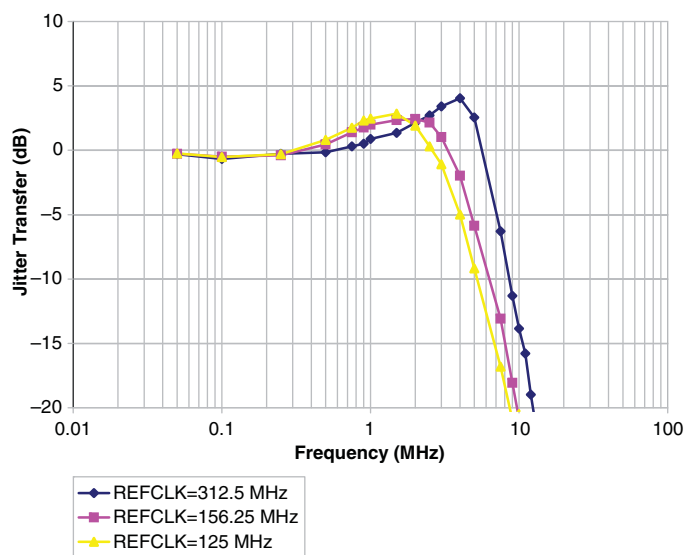


Figure 3-15. Jitter Transfer – 2.5 Gbps

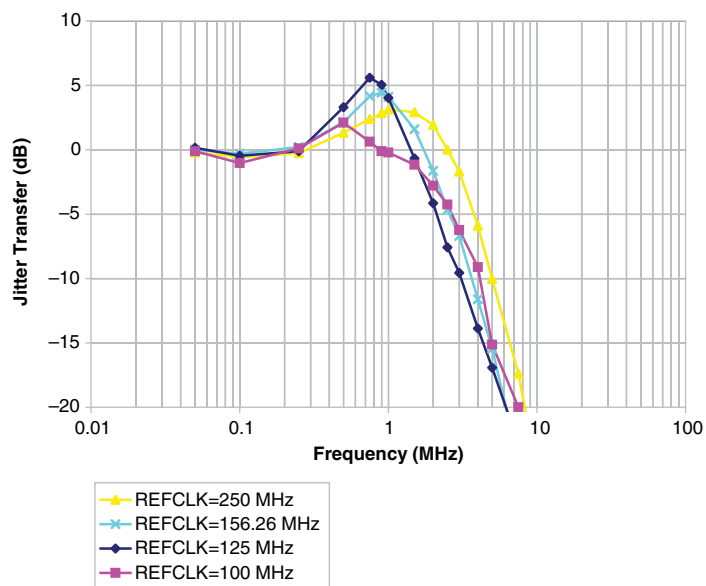
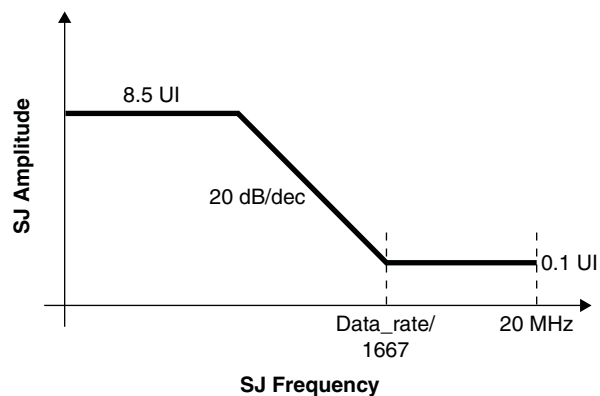


Figure 3-18. XAUI Sinusoidal Jitter Tolerance Mask



Note: The sinusoidal jitter tolerance is measured with at least 0.37 UIpp of Deterministic jitter (Dj) and the sum of Dj and Rj (random jitter) is at least 0.55 UIpp. Therefore, the sum of Dj, Rj and Sj (sinusoidal jitter) is at least 0.65 UIpp (Dj = 0.37, Rj = 0.18, Sj = 0.1).

LatticeECP3 sysCONFIG Port Timing Specifications

Over Recommended Operating Conditions

Parameter	Description	Min.	Max.	Units	
POR, Configuration Initialization, and Wakeup					
t _{ICFG}	Time from the Application of V _{CC} , V _{CCAUX} or V _{CCIO8} * (Whichever is the Last to Cross the POR Trip Point) to the Rising Edge of INITN	Master mode	—	23	ms
		Slave mode	—	6	ms
t _{VMC}	Time from t _{ICFG} to the Valid Master MCLK	—	5	μs	
t _{PRGM}	PROGRAMN Low Time to Start Configuration	25	—	ns	
t _{PRGMRJ}	PROGRAMN Pin Pulse Rejection	—	10	ns	
t _{DPPINIT}	Delay Time from PROGRAMN Low to INITN Low	—	37	ns	
t _{DPPDONE}	Delay Time from PROGRAMN Low to DONE Low	—	37	ns	
t _{DINIT} ¹	PROGRAMN High to INITN High Delay	—	1	ms	
t _{MWC}	Additional Wake Master Clock Signals After DONE Pin is High	100	500	cycles	
t _{CZ}	MCLK From Active To Low To High-Z	—	300	ns	
t _{IODISS}	User I/O Disable from PROGRAMN Low	—	100	ns	
t _{IOENSS}	User I/O Enabled Time from CCLK Edge During Wake-up Sequence	—	100	ns	
All Configuration Modes					
t _{SUCDI}	Data Setup Time to CCLK/MCLK	5	—	ns	
t _{HCDI}	Data Hold Time to CCLK/MCLK	1	—	ns	
t _{CODO}	CCLK/MCLK to DOUT in Flowthrough Mode	-0.2	12	ns	
Slave Serial					
t _{SSCH}	CCLK Minimum High Pulse	5	—	ns	
t _{SSCL}	CCLK Minimum Low Pulse	5	—	ns	
f _{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave Parallel					
t _{SUCS}	CSN[1:0] Setup Time to CCLK/MCLK	7	—	ns	
t _{HCS}	CSN[1:0] Hold Time to CCLK/MCLK	1	—	ns	
t _{SUWD}	WRITEN Setup Time to CCLK/MCLK	7	—	ns	
t _{HWD}	WRITEN Hold Time to CCLK/MCLK	1	—	ns	
t _{DCB}	CCLK/MCLK to BUSY Delay Time	—	12	ns	
t _{CORD}	CCLK to Out for Read Data	—	12	ns	
t _{BSCH}	CCLK Minimum High Pulse	6	—	ns	
t _{BSCL}	CCLK Minimum Low Pulse	6	—	ns	
t _{BSCYC}	Byte Slave Cycle Time	30	—	ns	
f _{CCLK}	CCLK/MCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave SPI					
t _{CFGX}	INITN High to MCLK Low	—	80	ns	
t _{CSSPI}	INITN High to CSSPIN Low	0.2	2	μs	
t _{SOCDO}	MCLK Low to Output Valid	—	15	ns	
t _{CSPID}	CSSPIN[0:1] Low to First MCLK Edge Setup Time	0.3		μs	
f _{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
t _{SSCH}	CCLK Minimum High Pulse	5	—	ns	

Signal Descriptions

Signal Name	I/O	Description
General Purpose		
P[Edge] [Row/Column Number]_[A/B]	I/O	<p>[Edge] indicates the edge of the device on which the pad is located. Valid edge designations are L (Left), B (Bottom), R (Right), T (Top).</p> <p>[Row/Column Number] indicates the PFU row or the column of the device on which the PIC exists. When Edge is T (Top) or B (Bottom), only need to specify Column Number. When Edge is L (Left) or R (Right), only need to specify Row Number.</p> <p>[A/B] indicates the PIO within the PIC to which the pad is connected. Some of these user-programmable pins are shared with special function pins. These pins, when not used as special purpose pins, can be programmed as I/Os for user logic. During configuration the user-programmable I/Os are tri-stated with an internal pull-up resistor enabled. If any pin is not used (or not bonded to a package pin), it is also tri-stated with an internal pull-up resistor enabled after configuration.</p>
P[Edge][Row Number]E_[A/B/C/D]	I	These general purpose signals are input-only pins and are located near the PLLs.
GSRN	I	Global RESET signal (active low). Any I/O pin can be GSRN.
NC	—	No connect.
RESERVED	—	This pin is reserved and should not be connected to anything on the board.
GND	—	Ground. Dedicated pins.
V _{CC}	—	Power supply pins for core logic. Dedicated pins.
V _{CCAUX}	—	Auxiliary power supply pin. This dedicated pin powers all the differential and referenced input buffers.
V _{CCIOx}	—	Dedicated power supply pins for I/O bank x.
V _{CCA}	—	SERDES, transmit, receive, PLL and reference clock buffer power supply. All V _{CCA} supply pins must always be powered to the recommended operating voltage range. If no SERDES channels are used, connect V _{CCA} to V _{CC} .
V _{CCPLL} _[LOC]	—	General purpose PLL supply pins where LOC=L (left) or R (right).
V _{REF1_x} , V _{REF2_x}	—	Reference supply pins for I/O bank x. Pre-determined pins in each bank are assigned as V _{REF} inputs. When not used, they may be used as I/O pins.
VTTx	—	Power supply for on-chip termination of I/Os.
XRES ¹	—	10 kOhm +/-1% resistor must be connected between this pad and ground.
PLL, DLL and Clock Functions		
[LOC][num]_GPLL[T, C]_IN_[index]	I	General Purpose PLL (GPLL) input pads: LUM, LLM, RUM, RLM, num = row from center, T = true and C = complement, index A,B,C...at each side.
[LOC][num]_GPLL[T, C]_FB_[index]	I	Optional feedback GPLL input pads: LUM, LLM, RUM, RLM, num = row from center, T = true and C = complement, index A,B,C...at each side.
[LOC]0_GDLLT_IN_[index] ²	I/O	General Purpose DLL (GDLL) input pads where LOC=RUM or LUM, T is True Complement, index is A or B.
[LOC]0_GDLLT_FB_[index] ²	I/O	Optional feedback GDLL input pads where LOC=RUM or LUM, T is True Complement, index is A or B.
PCLK[T, C][n:0]_[3:0] ²	I/O	Primary Clock pads, T = true and C = complement, n per side, indexed by bank and 0, 1, 2, 3 within bank.

Date	Version	Section	Change Summary
March 2010	01.6	Architecture	Added Read-Before-Write information.
		DC and Switching Characteristics	Added footnote #6 to Maximum I/O Buffer Speed table. Corrected minimum operating conditions for input and output differential voltages in the Point-to-Point LVDS table.
		Pinout Information	Added pin information for the LatticeECP3-70EA and LatticeECP3-95EA devices.
		Ordering Information	Added ordering part numbers for the LatticeECP3-70EA and LatticeECP3-95EA devices.
			Removed dual mark information.
November 2009	01.5	Introduction	Updated Embedded SERDES features. Added SONET/SDH to Embedded SERDES protocols.
		Architecture	Updated Figure 2-4, General Purpose PLL Diagram. Updated SONET/SDH to SERDES and PCS protocols.
			Updated Table 2-13, SERDES Standard Support to include SONET/SDH and updated footnote 2.
		DC and Switching Characteristics	Added footnote to ESD Performance table.
			Updated SERDES Power Supply Requirements table and footnotes.
			Updated Maximum I/O Buffer Speed table.
			Updated Pin-to-Pin Performance table.
			Updated sysCLOCK PLL Timing table.
			Updated DLL timing table.
			Updated High-Speed Data Transmitter tables.
			Updated High-Speed Data Receiver table.
			Updated footnote for Receiver Total Jitter Tolerance Specification table.
			Updated Periodic Receiver Jitter Tolerance Specification table.
			Updated SERDES External Reference Clock Specification table.
			Updated PCI Express Electrical and Timing AC and DC Characteristics.
			Deleted Reference Clock table for PCI Express Electrical and Timing AC and DC Characteristics.
			Updated SMPTE AC/DC Characteristics Transmit table.
			Updated Mini LVDS table.
			Updated RSDS table.
			Added Supply Current (Standby) table for EA devices.
			Updated Internal Switching Characteristics table.
			Updated Register-to-Register Performance table.
			Added HDMI Electrical and Timing Characteristics data.
			Updated Family Timing Adders table.
			Updated sysCONFIG Port Timing Specifications table.
			Updated Recommended Operating Conditions table.
			Updated Hot Socket Specifications table.
			Updated Single-Ended DC table.
			Updated TRLVDS table and figure.
			Updated Serial Data Input Specifications table.
			Updated HDMI Transmit and Receive table.
		Ordering Information	Added LFE3-150EA "TW" devices and footnotes to the Commercial and Industrial tables.